

## **Description**

The IRLZ44NPBF uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.



**TO-220** 

#### **General Features**

 $V_{DS} = 60V, I_{D} = 60A$ 

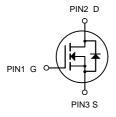
 $R_{DS(ON)} < 20m \Omega$  @  $V_{GS}=10V$ 

# **Application**

High efficiency switch mode power supplies

Power factor correction

Electronic lamp ballast



N-Channel MOSFET

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
IRLZ44NPBF	TO-220	HXY MOSFET	50

## Absolute Maximum Ratings@T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	60	V
VGS	Gate-Source Voltage	<u>+</u> 20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Drain Current	60	Α
IDM	Pulsed Drain Current <sup>1</sup>	240	Α
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation	120	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C



# Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage (Note 1)	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	60	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	60	68	-	nA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.0	-	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =25A	-	17	20	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =30V,I <sub>D</sub> =40A	15	-	-	S
Input Capacitance	C <sub>lss</sub>	\/ -25\/\/ -0\/	-	4050	-	PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =25V, $V_{GS}$ =0V, F=1.0MHz	-	430	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F-1.0WI1Z	-	110	-	PF
Turn-on Delay Time	t <sub>d(on)</sub>		-	60	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =30V,I <sub>D</sub> =40A	-	185	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_G$ =50 $\Omega$ (Note 2)	-	75	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	60	-	nS
Total Gate Charge	$Q_g$	\/ 20\/ L 40A	-	39	-	nC
Gate-Source Charge	$Q_{gs}$	$V_{DS}=30V,I_{D}=40A,$ $V_{GS}=10V^{(Note\ 2)}$	-	9.3	-	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	13	-	nC
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =60A	-		1.5	V
Diode Forward Current (Note 2)	Is		-	-	60	А

#### Notes:

<sup>1.</sup> Repetitive Rating: Pulse width limited by maximum junction temperature.

**<sup>2.</sup>** Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.



# **Typical Electrical**

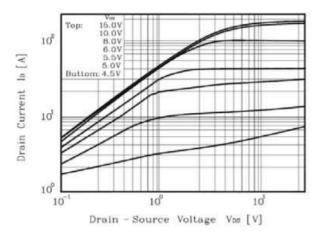


Figure 1. On Region Characteristics

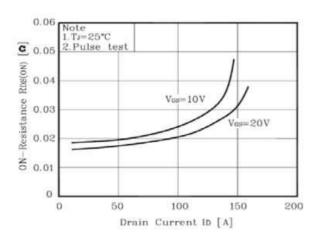


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

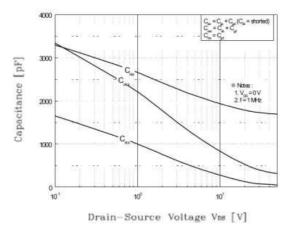


Figure 5. Capacitance Characteristics

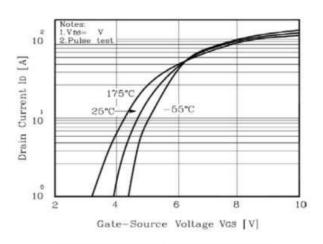


Figure 2. Transfer Characteristics

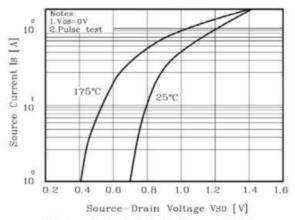


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

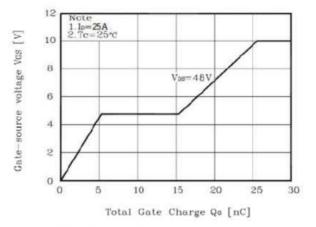


Figure 6. Gate Charge Characteristics



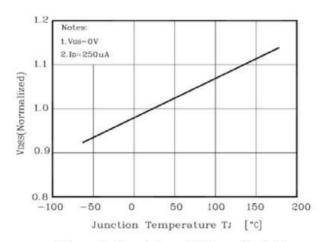


Figure 7. Breakdown Voltage Variation vs Temperature

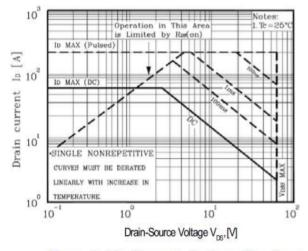


Figure 9. Maximum Safe Operating Area

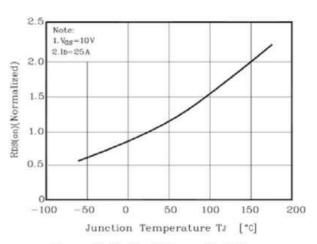


Figure 8. On-Resistance Variation vs Temperature

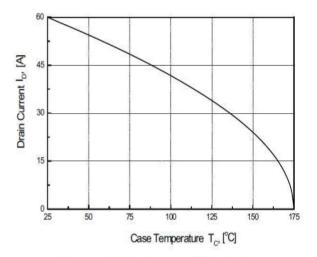


Figure 10. Maximum Drain Current vs Case Temperature

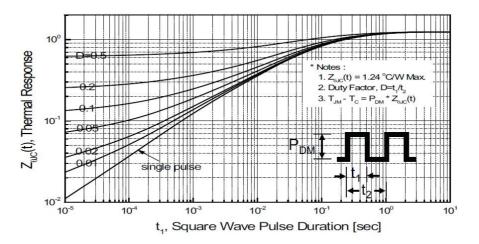
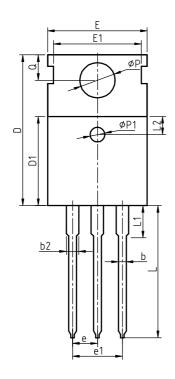
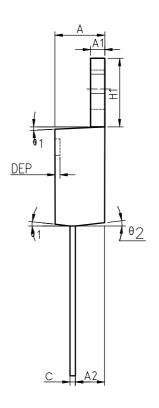


Figure 11. Transient Thermal Response Curve

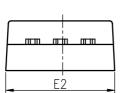


# Package Information TO-220





## COMMON DIMENSIONS



SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
Α	4.40	4.57	4.70	0. 173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1. 27	1.36	0.046	0.050	0.054
С	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9. 10	9. 20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
Ε	9.80	10.00	10.20	0. 386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
е		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0. 252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
Р	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0. 107	0.110	0. 113
θ 1	5°	7°	9°	5°	7°	9°
θ 2	1°	3°	5°	1°	3°	5°
θ 3	1°	3°	5°	1°	3°	5°



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